OPE5194

The **OPE5194** is GaAs infrared emitting diode that is designed for low forward voltage and high reliability. This device is optimized for efficiency at emission wavelength 940nm and has a high radiant efficiency over a wide range of forward current. This device is packaged T1-3/4 plastic package and has narrow beam angle with lensed package and cup frame.

FEATURES

- High-output power
- Narrow beam angle
- High reliability
- Available for pulse operating
- Low cost

APPLICATIONS

- Optical emitters
- Optical switches
- Smoke sensors
- IR remote control
- IR sound transmission

STORAGE

• Condition: 5°C~35°C,R.H.60%

• Terms: within 3 months from production date

• Remark : Once the package is opened, the products should be used within a day. Otherwise, it should be keeping in a damp proof box with desiccants.

* Please take proper steps in order to secure reliability and safety in required conditions and environments for this device.

Tolerance: ±0.2mm

MAXIMUM RATINGS

7	ra-25°C	١
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Item	Symbol	Rating	Unit	
Power Dissipation	P_{D}	150	mW	
Forward current	I_F	100	mA	
Pulse forward current	I_{FP}	1.0	A	
Reverse voltage	V_R	5.0	V	
Operating temp.	Topr.	-25~ +85	°C	
Soldering temp. *2	Tsol.	260.	°C	

^{*1.} Duty ratio = 1/100, pulse width=0.1ms.

ELECTRO-OPTICALCHARACTERISTICS

 $(Ta=25^{\circ}C)$

Item	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward voltage	V_{F}	$I_F = 100 \text{mA}$		1.4	1.7	V
Reverse current	I_R	$V_R = 5V$			10	μA
Capacitance	Ct	f = 1 MHz		20		pF
Radiant intensity	Ie	$I_F=100mA$		55		mW/sr
Peak emission wavelength	λ_p	$I_F = 50 \text{mA}$		940		nm
Spectral bandwidth 50%	Δλ	$I_F = 50 \text{mA}$		45		nm
Half angle	ΔΘ	$I_F=100mA$		±10		deg.

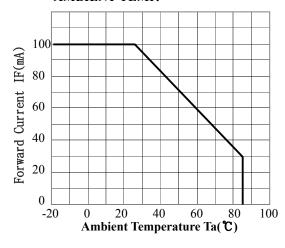
2- \square 0.5

Anode

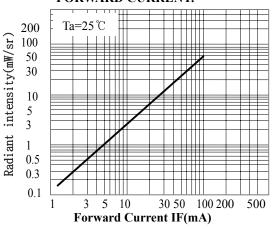
Cathode

^{*2.}Lead Soldering Temperature (2mm from case for 5sec.).

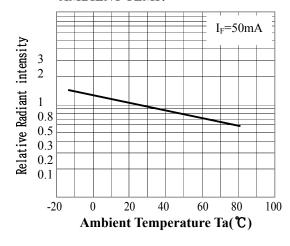
• FORWARD CURRENT Vs. AMBIENT TEMP.



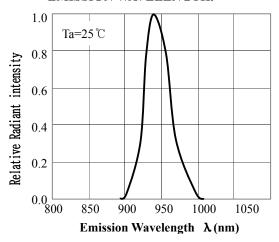
• RADIANT INTENSITY Vs. FORWARD CURRENT.



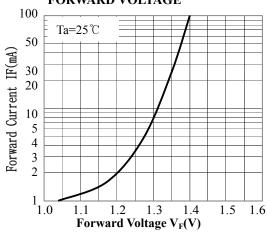
• RELATIVE RADIANT INTENSITY Vs. AMBIENT TEMP.



RELATIVE RADIANT INTENSITY Vs. EMISSION WAVELENGTH.



• FORWARD CURRENT Vs. FORWARD VOLTAGE



• ANGULAR DISPLACEMENT VS RELATIVE RADIANT INTENSITY

